



#9/aw/Ex. 782
1/16/03
4/14/03
Parent
10/010,484

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hshieh et al.

Serial No.: 10/010,484

Filed: November 20, 2001

Title: Trench MOSFET Device with Polycrystalline Silicon Source Contact Structure

Art Unit: 2826

Examiner: Tan N. Tran

Docket No.: GS 150

Assistant Commissioner for Patents
Washington, D.C. 20231

AMENDMENT

Sir:

In response to the Office Action dated December 4, 2002 (Paper No. 8), kindly consider the following response. In addition, any deficiencies may be charged to deposit account No. 50-1047.

IN THE CLAIMS

Please amend Claims 1 and 16 as follows:

1. (Amended) A trench MOSFET transistor device comprising:

04/15/2003 DSASFAI 0000005 3010484 a silicon substrate of a first conductivity type;

01 FC:1251 110.20 silicon epitaxial layer of said first conductivity type over said substrate, said epitaxial layer having a lower majority carrier concentration than said substrate;

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a trench extending into said epitaxial layer from an upper surface of said epitaxial layer; an insulating layer lining at least a portion of said trench;